

TO-126 Plastic-Encapsulate Transistors

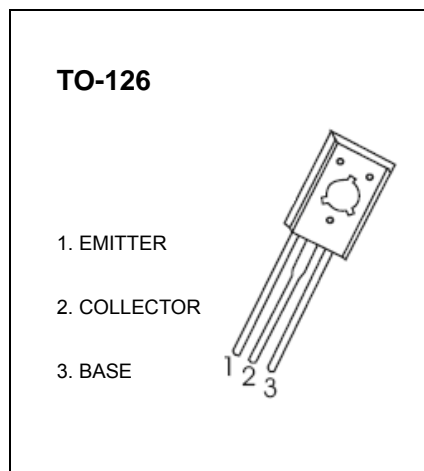
BD433/435/437 TRANSISTOR (NPN)

FEATURES

- Amplifier and Switching Applications

MAXIMUM RATINGS (Ta=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CB0}	Collector-Base Voltage	BD433	22
		BD435	32
		BD437	45
V _{CEO}	Collector-Emitter Voltage	BD433	22
		BD435	32
		BD437	45
V _{EBO}	Emitter-Base Voltage	5	V
I _C	Collector Current –Continuous	4	A
P _C	Collector Power Dissipation	1.25	W
T _J	Junction Temperature	150	°C
T _{stg}	Storage Temperature	-55-150	°C



ELECTRICAL CHARACTERISTICS (Ta=25°C unless otherwise specified)

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	V _{(BR)CBO}	BD433	22			V
		BD435	32			
		BD437	45			
Collector-emitter breakdown voltage	V _{CE(SUS)} ⁽¹⁾	BD433	22			V
		BD435	32			
		BD437	45			
Emitter-base breakdown voltage	V _{(BR)EBO}	I _E =100μA, I _C =0	5			V
Collector cut-off current	I _{CBO}	V _{CB} =22V, I _E =0	BD433			100
		V _{CB} =32V, I _E =0	BD435			
		V _{CB} =45V, I _E =0	BD437			
Collector cut-off current	I _{CEO}	V _{CE} =22V, I _E =0	BD433			100
		V _{CE} =32V, I _E =0	BD435			
		V _{CE} =45V, I _E =0	BD437			
Emitter cut-off current	I _{EBO}	V _{EB} =5V, I _E =0			1	mA
DC current gain	h _{FE(1)} ⁽¹⁾	V _{CE} =1V, I _C =500mA	85		375	
	h _{FE(2)} ⁽¹⁾	V _{CE} =5V, I _C =10mA	BD433/BD435	40		
			BD437	30		
h _{FE(3)} ⁽¹⁾	V _{CE} =1V, I _C =2A	BD433/BD435	50			
		BD437	40			
Collector-emitter saturation voltage	V _{CE(sat)} ⁽¹⁾	I _C =2A, I _B =0.2A			0.5 0.6	V
Base-emitter voltage	V _{BE} ⁽¹⁾	V _{CE} =1V, I _C =2A			1.1 1.2	V
Transition frequency	f _T	V _{CE} =1V, I _C =250mA	3			MHz

⁽¹⁾Pulse test.